L Number	Hits	Search Text	DB	Time stamp
82	2	("6674667").PN.	USPAT;	2004/03/21 14:02
			US-PGPUB;	
			EPO; JPO; DERWENT	
83	3	"20020110033" or (("6674667").PN.)	USPAT;	2004/03/21 14:02
03		20020110033 01 ((0074001).114.)	US-PGPUB;	2004/05/21 14.02
			EPO; JPO;	
			DERWENT	
81	2	"20020110033"	USPAT;	2004/03/21 14:02
			US-PGPUB;	
			EPO; JPO;	
ا ا	40705	mantal and avide and assuring advantage and field and affect and	DERWENT	2004/02/24 44-04
84	12725	metal adj oxide adj semiconductor adj field adj effect adj transistor	USPAT; US-PGPUB;	2004/03/21 14:04
		transistor	EPO; JPO;	
			DERWENT	
87	3	apply\$6 adj2 third adj voltage near1 potential adj3 gate	USPAT;	2004/03/21 14:05
			US-PGPUB;	
			EPO; JPO;	
	_		DERWENT	
88	3	apply\$6 adj2 third adj3 voltage near1 potential adj3 gate	USPAT;	2004/03/21 14:15
			US-PGPUB;	
			EPO; JPO; DERWENT	
85	5	apply\$6 adj2 first adj voltage near1 potential adj3 source	USPAT;	2004/03/21 14:08
00	9	apprywo adje mist adj voltage near i potential adjo source	US-PGPUB:	2004/03/21 14:00
			EPO; JPO;	
			DERWENT	
86	. 6	apply\$6 adj2 second adj voltage near1 potential adj3 drain	USPAT;	2004/03/21 14:12
			US-PGPUB;	
			EPO; JPO;	
00	_	(annlu@C adiQ first adi valtana maart natantial adiQ assura) ar	DERWENT	2004/02/24 44.42
89	5	(apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain)	USPAT; US-PGPUB;	2004/03/21 14:12
		and gate adj1 oxide	EPO; JPO;	
		and gate day i oxide	DERWENT	
90	4	((apply\$6 adj2 first adj voltage near1 potential adj3 source) or	USPAT;	2004/03/21 14:13
		(apply\$6 adj2 second adj voltage near1 potential adj3 drain)	US-PGPUB;	
		and gate adj1 oxide) and conduction adj1 channel	EPO; JPO;	
	4	///	DERWENT	0004/00/04 44 44
91	1	(((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain)	USPAT; US-PGPUB;	2004/03/21 14:14
		and gate adj1 oxide) and conduction adj1 channel) and	EPO; JPO;	
		negative adj gate adj1 potential near3 conduction adj1 channel	DERWENT	
92	1	(((apply\$6 adj2 first adj voltage near1 potential adj3 source) or	USPAT;	2004/03/21 14:14
		(apply\$6 adj2 second adj voltage near1 potential adj3 drain)	US-PGPUB;	
		and gate adj1 oxide) and conduction adj1 channel) and	EPO; JPO;	
	_	negative adj gate adj1 potential	DERWENT	0004/00/04 11 1-
94	0	apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate	USPAT;	2004/03/21 14:15
		near5 MOSFEt	US-PGPUB; EPO; JPO;	
			DERWENT	
95	5	apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate	USPAT;	2004/03/21 14:49
	-	, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
		(#14.054.054B)	DERWENT	00011001511165
97	18	(("4,051,354") or ("5,324,681") or ("5,327,380") or	USPAT;	2004/03/21 14:20
		("5,493,141") or ("5,764,096") or ("5,768,192") or ("5,781,477") or ("6,038,168") or ("6,229,733")).PN.	US-PGPUB; EPO; JPO;	
		01 (0,030, 100) 01 (0,223,133)).PN.	DERWENT	
98	809	apply\$6 adj2 negative adj3 voltage adj3 gate	USPAT;	2004/03/21 14:49
	303	The state of the s	US-PGPUB;	
			EPO; JPO;	
			DERWENT	

99	4802	apply\$6 adj2 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	USPAT; US-PGPUB;	2004/03/21 14:49
			EPO; JPO; DERWENT	
100	4802	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT:	2004/03/21 14:50
		circuit) bias adj3 voltage adj3 gate	US-PGPUB;	
			EPO; JPO;	
101	1039	(apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ	DERWENT USPAT:	2004/03/21 14:50
	1000	circuit) bias adj3 voltage adj3 gate) and MOSFET	US-PGPUB;	2004/00/21 14:00
			EPO; JPO;	
400	200		DERWENT	2004/02/04 44.50
102	260	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT; US-PGPUB:	2004/03/21 14:50
		anoun, side daje vokage daje gate modre modret	EPO; JPO;	
			DERWENT	
104	103	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	US-PGPUB; EPO; JPO;	2004/03/21 14:51
		Gircuit) bias aujo voitage aujo gate nearo mosiet	DERWENT	
103	157	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/03/21 14:51
		circuit) bias adj3 voltage adj3 gate near5 mosfet		
105	150	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/03/21 14:53
106	150	circuit) bias adj1 voltage adj3 gate near5 mosfet apply adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/03/21 14:52
100	130	circuit) bias adj1 voltage adj3 gate near5 mosfet	001 71	2004/03/21 14.32
107	150	appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/03/21 14:54
		circuit) bias adj1 voltage adj3 gate near5 mosfet		
108	30	(appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/03/21 14:54
		circuit) bias adj1 voltage adj3 gate near5 mosfet) and negative		
		adj1 voltage		